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MACRONIX
INTERNATIONAL Co., LTD.

MX25L3255E

MX25L3255E
HIGH PERFORMANCE
SERIAL FLASH SPECIFICATION

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32M-BIT [x 1/x 2/x 4] CMOS MXSMIO™ (SERIAL MULTI I/O) FLASH MEMORY**1. FEATURES****GENERAL**

- Serial Peripheral Interface compatible -- Mode 0 and Mode 3
- 33,554,432 x 1 bit structure or 16,777,216 x 2 bits (two I/O mode) structure or 8,388,608 x 4 bits (four I/O mode) structure
- 1024 Equal Sectors with 4K bytes each
 - Any Sector can be erased individually
- 128 Equal Blocks with 32K bytes each
 - Any Block can be erased individually
- 64 Equal Blocks with 64K bytes each
 - Any Block can be erased individually
- Power Supply Operation
 - 2.7 to 3.6 volt for read, erase, and program operations
- Latch-up protected to 100mA from -1V to Vcc +1V

PERFORMANCE

- High Performance
 - VCC = 2.7~3.6V
 - Normal read
 - 50MHz
 - Fast read
 - 1 I/O: 104MHz with 8 dummy cycles
 - 2 I/O: 86MHz with 4 dummy cycles for 2READ instruction
 - 4 I/O: Up to 104MHz for 4READ instruction
 - Configurable dummy cycle number for 4READ operation
 - Fast program time: 1.4ms(typ.) and 5ms(max.)/page (256-byte per page)
 - Byte program time: 12us (typical)
 - Continuous Program mode (automatically increase address under word program mode)
 - Fast erase time: 60ms (typ.)/sector (4K-byte per sector) ; 0.7s(typ.) /block (64K-byte per block); 25s(typ.) / chip
- Low Power Consumption
 - Low active read current: 19mA(max.) at 104MHz, 10mA(max.) at 33MHz
 - Low active programming current: 25mA (max.)
 - Low active erase current: 25mA (max.)
 - Low standby current: 80uA (max.)
 - Deep power down current: 40uA (max.)
- Typical 100,000 erase/program cycles
- 20 years data retention

SOFTWARE FEATURES

- Input Data Format
 - 1-byte Command code
- Advanced Security Features
 - BP0-BP3 block group protect
 - Flexible individual block protect when OTP WPSEL=1
 - Additional 4K bits secured OTP for unique identifier
 - Permanent Lock
 - Read Protection function
- Auto Erase and Auto Program Algorithms
 - Automatically erases and verifies data at selected sector
 - Automatically programs and verifies data at selected page by an internal algorithm that automatically times the program pulse width (Any page to be programmed should have page in the erased state first.)
- Status Register Feature
- Electronic Identification
 - JEDEC 1-byte Manufacturer ID and 2-byte Device ID
 - RES command for 1-byte Device ID
 - The REMS,REMS2, REMS4 commands for 1-byte Manufacturer ID and 1-byte Device ID
- Support Serial Flash Discoverable Parameters (SFDP) mode

HARDWARE FEATURES

- SCLK Input
 - Serial clock input
- SI/SIO0
 - Serial Data Input or Serial Data Input/Output for 2 x I/O mode and 4 x I/O mode
- SO/SIO1
 - Serial Data Output or Serial Data Input/Output for 2 x I/O mode and 4 x I/O mode
- WP#/SIO2
 - Hardware write protection or serial data Input/Output for 4 x I/O mode
- HOLD#/SIO3
 - To pause the device without deselecting the device or serial data Input/Output for 4 x I/O mode
- PACKAGE
 - 8-pin SOP (200mil)
 - 24-ball TFBGA (6x8mm)
 - **All devices are RoHS Compliant**

2. GENERAL DESCRIPTION

MX25L3255E is 32Mb bits serial Flash memory, which is configured as 4,194,304 x 8 internally. When it is in two or four I/O mode, the structure becomes 16,777,216 bits x 2 or 8,388,608 bits x 4. MX25L3255E feature a serial peripheral interface and software protocol allowing operation on a simple 3-wire bus while it is in single I/O mode. The three bus signals are a clock input (SCLK), a serial data input (SI), and a serial data output (SO). Serial access to the device is enabled by CS# input.

MX25L3255E, MXSMIO™ (Serial Multi I/O) flash memory, provides sequential read operation on whole chip and multi-I/O features.

When it is in dual I/O mode, the SI pin and SO pin become SIO0 pin and SIO1 pin for address/dummy bits input and data output. When it is in quad I/O mode, the SI pin, SO pin, WP# pin and HOLD# pin become SIO0 pin, SIO1 pin, SIO2 pin and SIO3 pin for address/dummy bits input and data Input/Output.

After program/erase command is issued, auto program/erase algorithms which program/erase and verify the specified page or sector/block locations will be executed. Program command is executed on byte basis, or page (256 bytes) basis, or word basis for Continuous Program mode, and erase command is executed on sector (4K-byte), block (32K-byte/64K-byte), or whole chip basis.

To provide user with ease of interface, a status register is included to indicate the status of the chip. The status read command can be issued to detect completion status of a program or erase operation via WIP bit.

When the device is not in operation and CS# is high, it is put in standby mode and draws less than 40uA DC current.

The MX25L3255E utilizes Macronix's proprietary memory cell, which reliably stores memory contents even after 100,000 program and erase cycles.

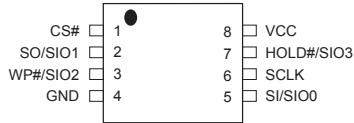
Table 1. Read Performance

Numbers of Dummy Cycles	4 I/O
6	86*
8	104

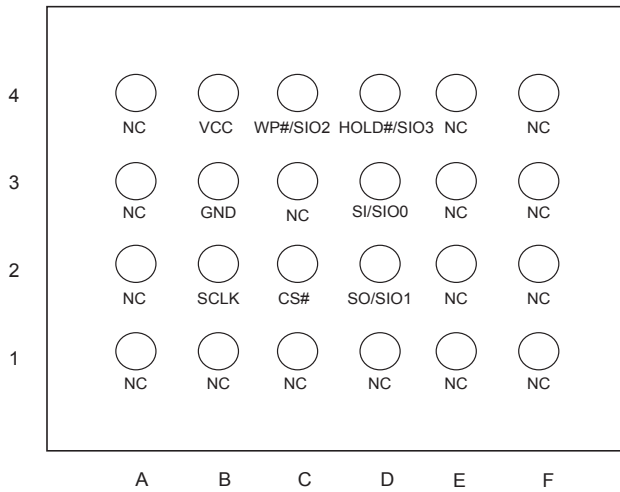
Note: *means default status

3. PIN CONFIGURATION

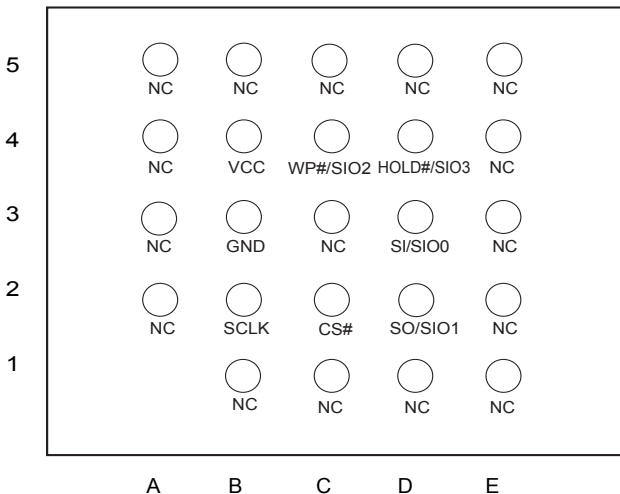
8-PIN SOP (200mil)



24-Ball TFBGA (6x8 mm, 4x6 Ball Array)



24-Ball TFBGA (6x8 mm, 5x5 Ball Array)

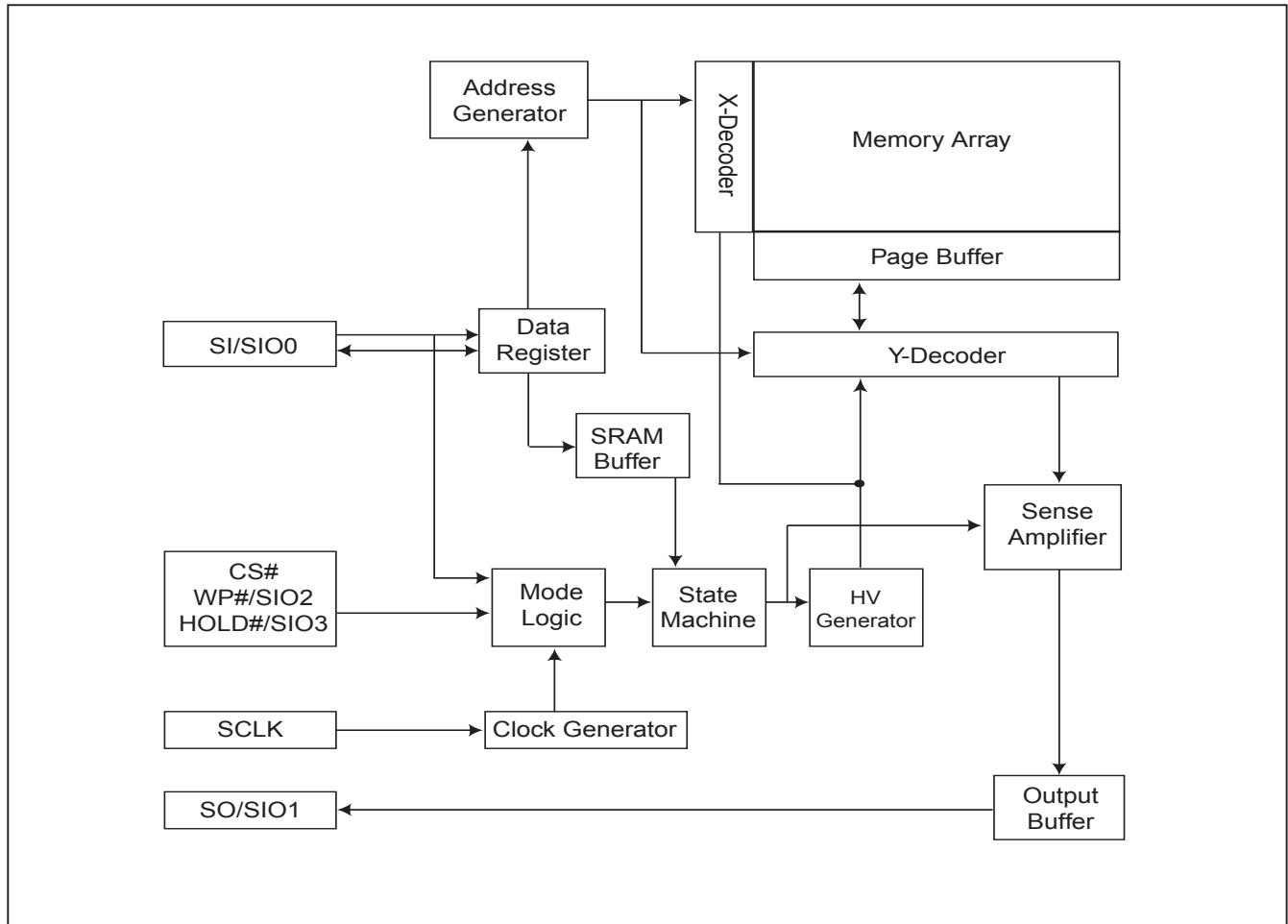


4. PIN DESCRIPTION

SYMBOL	DESCRIPTION
CS#	Chip Select
SI/SIO0	Serial Data Input (for 1xI/O)/ Serial Data Input & Output (for 2xI/O or 4xI/O mode)
SO/SIO1	Serial Data Output (for 1xI/O)/Serial Data Input & Output (for 2xI/O or 4xI/O mode)
SCLK	Clock Input
WP#/SIO2	Write protection: connect to GND or Serial Data Input & Output (for 4xI/O mode)
HOLD#/SIO3	To pause the device without deselecting the device or Serial data Input/Output for 4 x I/O mode
VCC	+ 3.0V Power Supply
GND	Ground
NC	No Connection

Note:

1. The HOLD# pin is internal pull high.

5. BLOCK DIAGRAM

6. DATA PROTECTION

During power transition, there may be some false system level signals which result in inadvertent erasure or programming. The device is designed to protect itself from these accidental write cycles.

The state machine will be reset as standby mode automatically during power up. In addition, the control register architecture of the device constrains that the memory contents can only be changed after specific command sequences have completed successfully.

In the following, there are several features to protect the system from the accidental write cycles during VCC power-up and power-down or from system noise.

- Valid command length checking: The command length will be checked whether it is at byte base and completed on byte boundary.
- Write Enable (WREN) command: WREN command is required to set the Write Enable Latch bit (WEL) before other command to change data. The WEL bit will return to reset stage under following situation:
 - Power-up
 - Write Disable (WRDI) command completion
 - Write Status Register (WRSR) command completion
 - Page Program (PP, 4PP) command completion
 - Continuous Program mode (CP) instruction completion
 - Sector Erase (SE) command completion
 - Block Erase (BE, BE32K) command completion
 - Chip Erase (CE) command completion
 - Single Block Lock/Unlock (SBLK/SBULK) instruction completion
 - Gang Block Lock/Unlock (GBLK/GBULK) instruction completion
 - Permanent Lock (PLOCK) Instruction Completion
 - Write Read Lock Register (WRLCR) Command Completion
- Deep Power Down Mode: By entering deep power down mode, the flash device also is under protected from writing all commands except Release from Deep Power Down mode command (RDP) and Read Electronic Signature command (RES).

I. Block lock protection

- The Software Protected Mode (SPM) uses (BP3, BP2, BP1, BP0) bits to allow part of memory to be protected as read only. The protected area definition is shown as table of "[Table 2. Protected Area Sizes](#)", the protected areas are more flexible which may protect various areas by setting value of BP0-BP3 bits.
- The Hardware Protected Mode (HPM) uses WP#/SIO2 to protect the (BP3, BP2, BP1, BP0) bits and SRWD bit. If the system goes into four I/O mode, the feature of HPM will be disabled.
- MX25L3255E provides individual block (or sector) write protect & unprotect. User may enter the mode with WPSEL command and conduct individual block (or sector) write protect with SBLK instruction, or SBULK for individual block (or sector) unprotect. Under the mode, user may conduct whole chip (all blocks) protect with GBLK instruction and unlock the whole chip with GBULK instruction.

Table 2. Protected Area Sizes

Protected Area Sizes (T/B bit = 0)

Status bit				Protect Level
BP3	BP2	BP1	BP0	32Mb
0	0	0	0	0 (none)
0	0	0	1	1 (1block, block 63rd)
0	0	1	0	2 (2blocks, block 62nd-63rd)
0	0	1	1	3 (4blocks, block 60th-63rd)
0	1	0	0	4 (8blocks, block 56th-63rd)
0	1	0	1	5 (16blocks, block 48th-63rd)
0	1	1	0	6 (32blocks, block 32nd-63rd)
0	1	1	1	7 (64blocks, protect all)
1	0	0	0	8 (64blocks, protect all)
1	0	0	1	9 (64blocks, protect all)
1	0	1	0	10 (64blocks, protect all)
1	0	1	1	11 (64blocks, protect all)
1	1	0	0	12 (64blocks, protect all)
1	1	0	1	13 (64blocks, protect all)
1	1	1	0	14 (64blocks, protect all)
1	1	1	1	15 (64blocks, protect all)

Protected Area Sizes (T/B bit = 1)

Status bit				Protect Level
BP3	BP2	BP1	BP0	32Mb
0	0	0	0	0 (none)
0	0	0	1	1 (1block, block 0th)
0	0	1	0	2 (2blocks, block 0th-1st)
0	0	1	1	3 (4blocks, block 0th-3rd)
0	1	0	0	4 (8blocks, block 0th-7th)
0	1	0	1	5 (16blocks, block 0th-15th)
0	1	1	0	6 (32blocks, block 0th-31st)
0	1	1	1	7 (64blocks, protect all)
1	0	0	0	8 (64blocks, protect all)
1	0	0	1	9 (64blocks, protect all)
1	0	1	0	10 (64blocks, protect all)
1	0	1	1	11 (64blocks, protect all)
1	1	0	0	12 (64blocks, protect all)
1	1	0	1	13 (64blocks, protect all)
1	1	1	0	14 (64blocks, protect all)
1	1	1	1	15 (64blocks, protect all)

Note: The device is ready to accept a Chip Erase instruction if, and only if, all Block Protect (BP3, BP2, BP1, BP0) are 0.

II. Additional 4K-bit secured OTP for unique identifier: to provide 4K-bit One-Time Program area for setting device unique serial number - Which may be set by factory or system maker.

- Security register bit 0 indicates whether the chip is locked by factory or not.
- To program the 4K-bit secured OTP by entering 4K-bit secured OTP mode (with ENSO command), and going through normal program procedure, and then exiting 4K-bit secured OTP mode by writing EXSO command.
- Customer may lock-down the customer lockable secured OTP by writing WRSCUR(write security register) command to set customer lock-down bit1 as "1". Please refer to table of "[Table 8. Security Register Definition](#)" for security register bit definition and table of "[Table 3. 4K-bit Secured OTP Definition](#)" for address range definition.

Note: Once lock-down whatever by factory or customer, it cannot be changed any more. While in 4K-bit Secured OTP mode, array access is not allowed.

Table 3. 4K-bit Secured OTP Definition

Address range	Size	Standard Factory Lock	Customer Lock
xxx000~xxx00F	128-bit	ESN (electrical serial number)	Determined by customer
xxx010~xxx1FF	3968-bit	N/A	

7. MEMORY ORGANIZATION

Table 4. Memory Organization

Block(64K-byte)	Block(32K-byte)	Sector (4K-byte)	Address Range	
63	127	1023	3FF000h	3FFFFFFh
		⋮		
		1016	3F8000h	3F8FFFh
		1015	3F7000h	3F7FFFh
	126	⋮		
		1008	3F0000h	3F0FFFh
		1007	3EF000h	3EFFFFh
		⋮		
62	125	1000	3E8000h	3E8FFFh
		⋮		
		999	3E7000h	3E7FFFh
		⋮		
	124	992	3E0000h	3E0FFFh
		⋮		
		991	3DF000h	3DFFFFh
		⋮		
61	123	984	3D8000h	3D8FFFh
		⋮		
		983	3D7000h	3D7FFFh
		⋮		
	122	976	3D0000h	3D0FFFh
		⋮		
		⋮		
		⋮		

individual block
lock/unlock unit:64K-byte

individual 16 sectors
lock/unlock unit:4K-byte

individual block
lock/unlock unit:64K-byte



2	5	47	02F000h	02FFFFh
		⋮		
		40	028000h	028FFFh
	4	39	027000h	027FFFh
		⋮		
1	3	32	020000h	020FFFh
		⋮		
		31	01F000h	01FFFFh
	2	24	018000h	018FFFh
		⋮		
		23	017000h	017FFFh
0	1	16	010000h	010FFFh
		⋮		
		15	00F000h	00FFFFh
	0	8	008000h	008FFFh
		⋮		
		7	007000h	007FFFh
		0	000000h	000FFFh

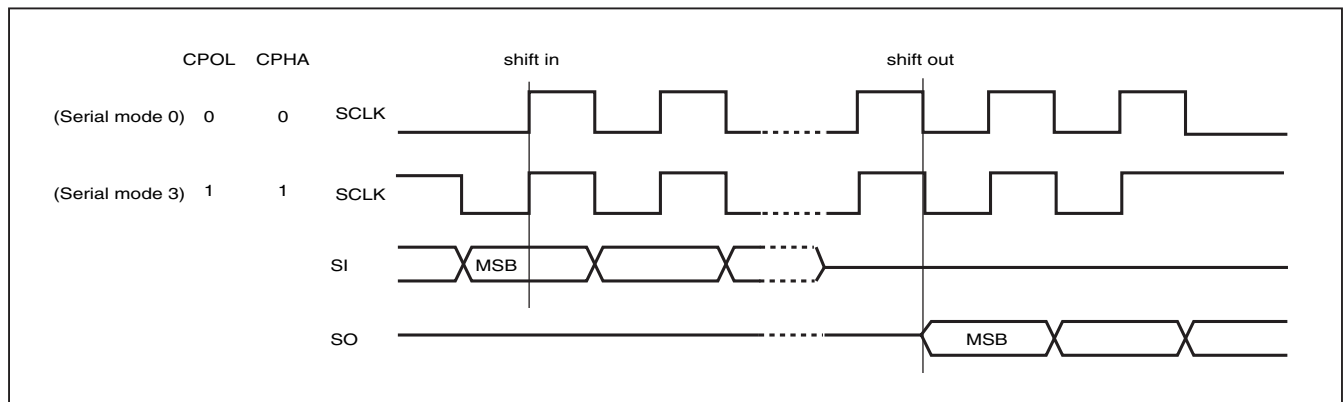
individual block
lock/unlock unit:64K-byte

individual 16 sectors
lock/unlock unit:4K-byte

8. DEVICE OPERATION

1. Before a command is issued, status register should be checked to ensure device is ready for the intended operation.
2. When incorrect command is inputted to this LSI, this LSI becomes standby mode and keeps the standby mode until next CS# falling edge. In standby mode, SO pin of this LSI should be High-Z.
3. When correct command is inputted to this LSI, this LSI becomes active mode and keeps the active mode until next CS# rising edge.
4. For standard single data rate serial mode, input data is latched on the rising edge of Serial Clock(SCLK) and data shifts out on the falling edge of SCLK. The difference of Serial mode 0 and mode 3 is shown as "[Figure 1. Serial Modes Supported \(for Normal Serial mode\)](#)".
5. For the following instructions: RDID, RDSR, RDSCUR, READ, FAST_READ, RDSFDP, 2READ, DREAD, 4READ, QREAD, RDBLOCK, RES, REMS, REMS2, REMS4, RDPLOCK, and RRLCR the shifted-in instruction sequence is followed by a data-out sequence. After any bit of data being shifted out, the CS# can be high. For the following instructions: WREN, WRDI, WRSR, SE, BE, BE32K, HPM, CE, PP, CP, 4PP, RDP, DP, WPSEL, SBLK, SBULK, GBLK, GBULK, ENSO, EXSO, WRSCUR, ESRY, DSRV, PLOCK, and WRLCR, the CS# must go high exactly at the byte boundary; otherwise, the instruction will be rejected and not executed.
6. During the progress of Write Status Register, Program, Erase operation, to access the memory array is neglected and not affect the current operation of Write Status Register, Program, Erase.

Figure 1. Serial Modes Supported (for Normal Serial mode)



Note:

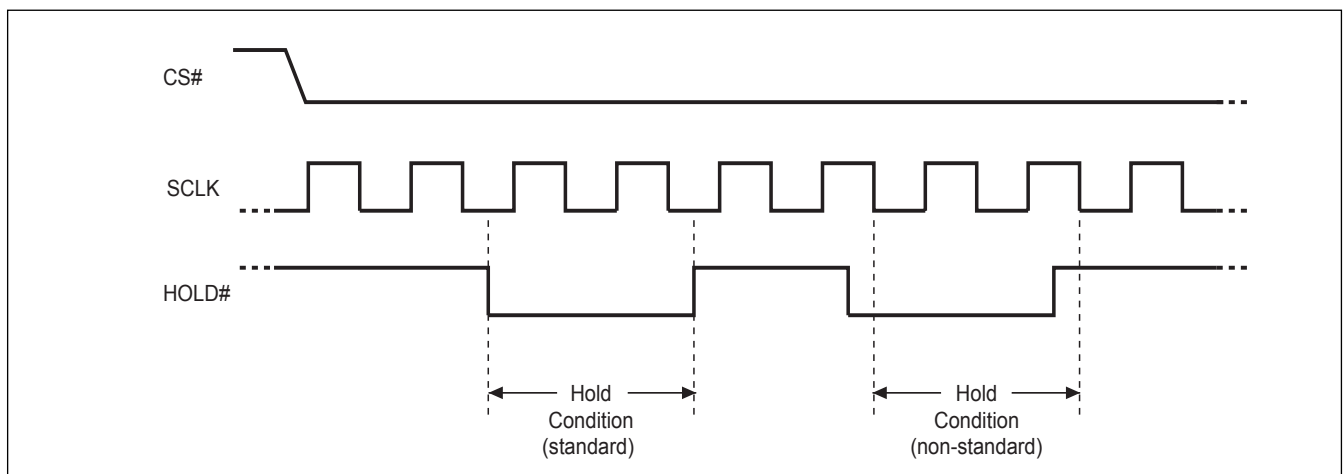
CPOL indicates clock polarity of Serial master, CPOL=1 for SCLK high while idle, CPOL=0 for SCLK low while not transmitting. CPHA indicates clock phase. The combination of CPOL bit and CPHA bit decides which Serial mode is supported.

9. HOLD FEATURE

HOLD# pin signal goes low to hold any serial communications with the device. The HOLD feature will not stop the operation of write status register, programming, or erasing in progress.

The operation of HOLD requires Chip Select (CS#) keeping low and starts on falling edge of HOLD# pin signal while Serial Clock (SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not start until Serial Clock signal being low). The HOLD condition ends on the rising edge of HOLD# pin signal while Serial Clock(SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not end until Serial Clock being low).

Figure 2. Hold Condition Operation



The Serial Data Output (SO) is high impedance, both Serial Data Input (SI) and Serial Clock (SCLK) are don't care during the HOLD operation. If Chip Select (CS#) drives high during HOLD operation, it will reset the internal logic of the device. To re-start communication with chip, the HOLD# must be at high and CS# must be at low.

Note: The HOLD feature is disabled during Quad I/O mode.

10. COMMAND DESCRIPTION

Table 5. Command Sets

Read Commands

I/O	1	1	2	2	4	4	4
Command	READ (normal read)	FAST READ (fast read data)	2READ (2 x I/O read command)	DREAD (1I / 2O read command)	W4READ	4READ (4 x I/O read command)	QREAD
1st byte	03 (hex)	0B (hex)	BB (hex)	3B (hex)	E7 (hex)	EB (hex)	6B (hex)
2nd byte	AD1(8)	AD1(8)	AD1(4)	AD1(8)	AD1(2)	AD1(2)	AD1(8)
3rd byte	AD2(8)	AD2(8)	AD2(4)	AD2(8)	AD2(2)	AD2(2)	AD2(8)
4th byte	AD3(8)	AD3(8)	AD3(4)	AD3(8)	AD3(2)	AD3(2)	AD3(8)
5th byte		Dummy(8)	Dummy(4)	Dummy(8)	Dummy(4)	Dummy*	Dummy(8)
Action	n bytes read out until CS# goes high	n bytes read out until CS# goes high	n bytes read out by 2 x I/O until CS# goes high		Quad I/O read with 4 dummy cycles	Quad I/O read with configurable dummy cycles	

Note: *Dummy cycle number will be different, depending on the bit7 (DC) setting of Configuration Register. Please refer to "[Configuration Register](#)" Table.

Other Commands

Command	WREN (write enable)	WRDI (write disable)	RDSR (read status register)	RDCR (read configuration register)	WRSR (write status/ configuration register)	4PP (quad page program)	SE (sector erase)
1st byte	06 (hex)	04 (hex)	05 (hex)	15 (hex)	01 (hex)	38 (hex)	20 (hex)
2nd byte					Values	AD1	AD1
3rd byte					Values	AD2	AD2
4th byte						AD3	AD3
Action	sets the (WEL) write enable latch bit	resets the (WEL) write enable latch bit	to read out the values of the status register	to read out the values of the configuration register	to write new values of the status register	quad input to program the selected page	to erase the selected sector

Command	BE 32K (block erase 32KB)	BE (block erase 64KB)	CE (chip erase)	PP (page program)	CP (continuous program)	DP (Deep power down)	RDP (Release from deep power down)
1st byte	52 (hex)	D8 (hex)	60 or C7 (hex)	02 (hex)	AD (hex)	B9 (hex)	AB (hex)
2nd byte	AD1	AD1		AD1	AD1		
3rd byte	AD2	AD2		AD2	AD2		
4th byte	AD3	AD3		AD3	AD3		
Action	to erase the selected 32KB block	to erase the selected 64KB block	to erase whole chip	to program the selected page	continuously program whole chip, the address is automatically increase	enters deep power down mode	release from deep power down mode

Command	RDID (read identification)	RES (read electronic ID)	REMS (read electronic manufacturer & device ID)	REMS2 (read electronic manufacturer & device ID)	REMS4 (read electronic manufacturer & device ID)	ENSO (enter secured OTP)	EXSO (exit secured OTP)
1st byte	9F (hex)	AB (hex)	90 (hex)	EF (hex)	DF (hex)	B1 (hex)	C1 (hex)
2nd byte		x	x	x	x		
3rd byte		x	x	x	x		
4th byte		x	ADD (Note 2)	ADD	ADD		
Action	outputs JEDEC ID: 1-byte Manufacturer ID & 2-byte Device ID	to read out 1-byte Device ID	output the Manufacturer ID & Device ID	output the Manufacturer ID & Device ID	output the Manufacturer ID & device ID	to enter the 4K-bit secured OTP mode	to exit the 4K-bit secured OTP mode

Command	RDSCUR (read security register)	WRSCUR (write security register)	SBLK (single block lock)	SBULK (single block unlock)	RDBLOCK (block protect read)	GBLK (gang block lock)	GBULK (gang block unlock)
1st byte	2B (hex)	2F (hex)	36 (hex)	39 (hex)	3C (hex)	7E (hex)	98 (hex)
2nd byte			AD1	AD1	AD1		
3rd byte			AD2	AD2	AD2		
4th byte			AD3	AD3	AD3		
Action	to read value of security register	to set the lock-down bit as "1" (once lock-down, cannot be update)	individual block (64K-byte) or sector (4K-byte) write protect	individual block (64K-byte) or sector (4K-byte) unprotect	read individual block or sector write protect status	whole chip write protect	whole chip unprotect

Command	NOP (No Operation)	RSTEN (Reset Enable)	RST (Reset Memory)	WPSEL (Write Protect Selection)	ESRY (enable SO to output RY/BY#)	DSRY (disable SO to output RY/BY#)	RDSFDP
1st byte	00 (hex)	66 (hex)	99 (hex)	68 (hex)	70 (hex)	80 (hex)	5A (hex)
2nd byte							AD1
3rd byte							AD2
4th byte							AD3
5th byte							Dummy
Action				to enter and enable individual block protect mode	to enable SO to output RY/BY# during CP mode	to disable SO to output RY/BY# during CP mode	n bytes read out until CS# goes high

Command	Release Read Enhanced	HPM (High Performance Enable Mode)
1st byte	FF (hex)	A3 (hex)
2nd byte		
3rd byte		
4th byte		
5th byte		
Action	All these commands FFh, 00h, AAh or 55h will escape the performance mode	Quad I/O high Performance mode

Note 1: The count base is 4-bit for ADD(2) and Dummy(2) because of 2 x I/O. And the MSB is on SI/SIO1 which is different from 1 x I/O condition.

Note 2: ADD=00H will output the manufacturer ID first and ADD=01H will output device ID first.

Note 3: It is not recommended to adopt any other code not in the command definition table, which will potentially enter the hidden mode.

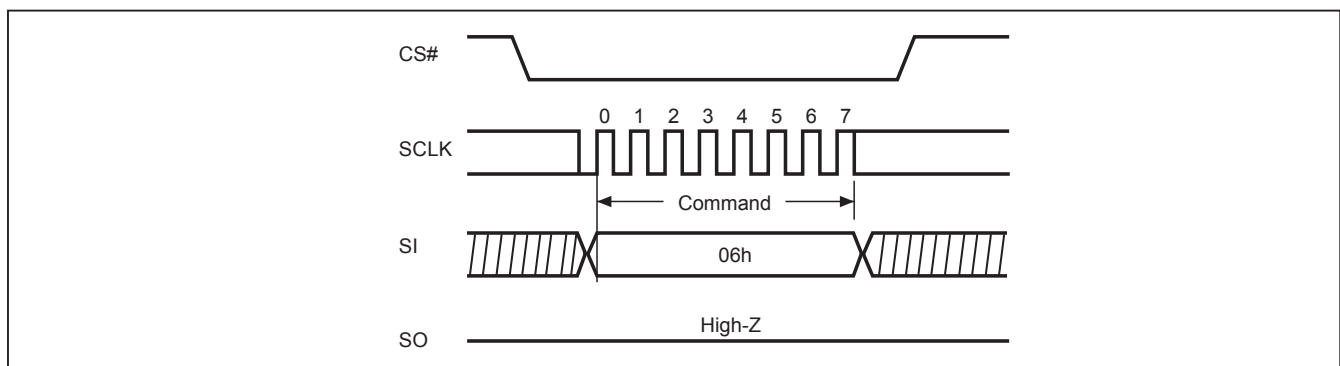
Note 4: Before executing RST command, RSTEN command must be executed. If there is any other command to interfere, the reset operation will be disabled.

10-1. Write Enable (WREN)

The Write Enable (WREN) instruction is for setting Write Enable Latch (WEL) bit. For those instructions like PP, 4PP, CP, SE, BE, BE32K, CE, WRSR, WRSCUR, WPSEL, SBLK, SBULK, GBLK and GBULK, which are intended to change the device content, should be set every time after the WREN instruction setting the WEL bit.

The sequence of issuing WREN instruction is: CS# goes low→ sending WREN instruction code→ CS# goes high.

The SIO[3:1] are don't care in this mode.

Figure 3. Write Enable (WREN) Sequence (Command 06)

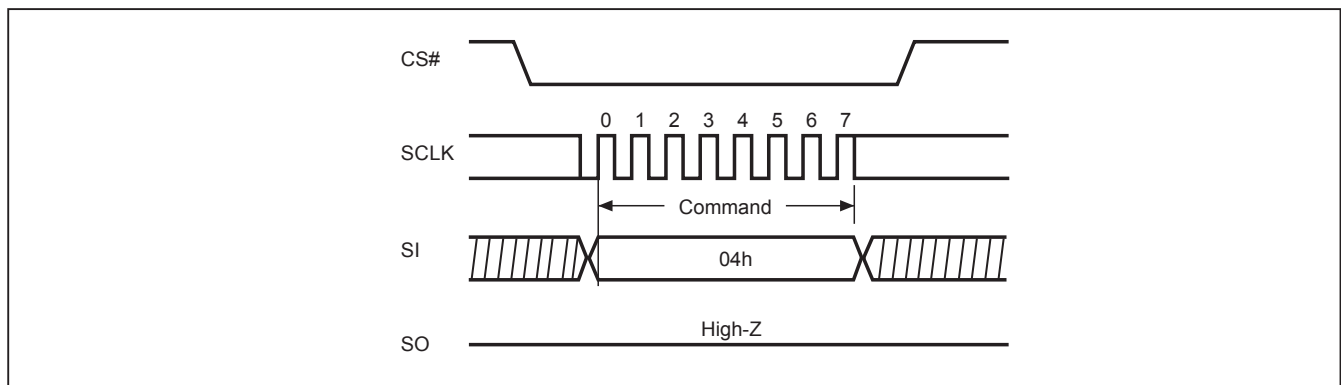
10-2. Write Disable (WRDI)

The Write Disable (WRDI) instruction is for resetting Write Enable Latch (WEL) bit.

The sequence of issuing WRDI instruction is: CS# goes low→ sending WRDI instruction code→ CS# goes high.

The WEL bit is reset by following situations:

- Power-up
- Write Disable (WRDI) instruction completion
- Write Status/Configuration Register (WRSR) instruction completion
- Page Program (PP, 4PP) instruction completion
- Sector Erase (SE) instruction completion
- Block Erase (BE, BE32K) instruction completion
- Chip Erase (CE) instruction completion
- Continuous Program mode (CP) instruction completion
- Single Block Lock/Unlock (SBLK/SBULK) instruction completion
- Gang Block Lock/Unlock (GBLK/GBULK) instruction completion

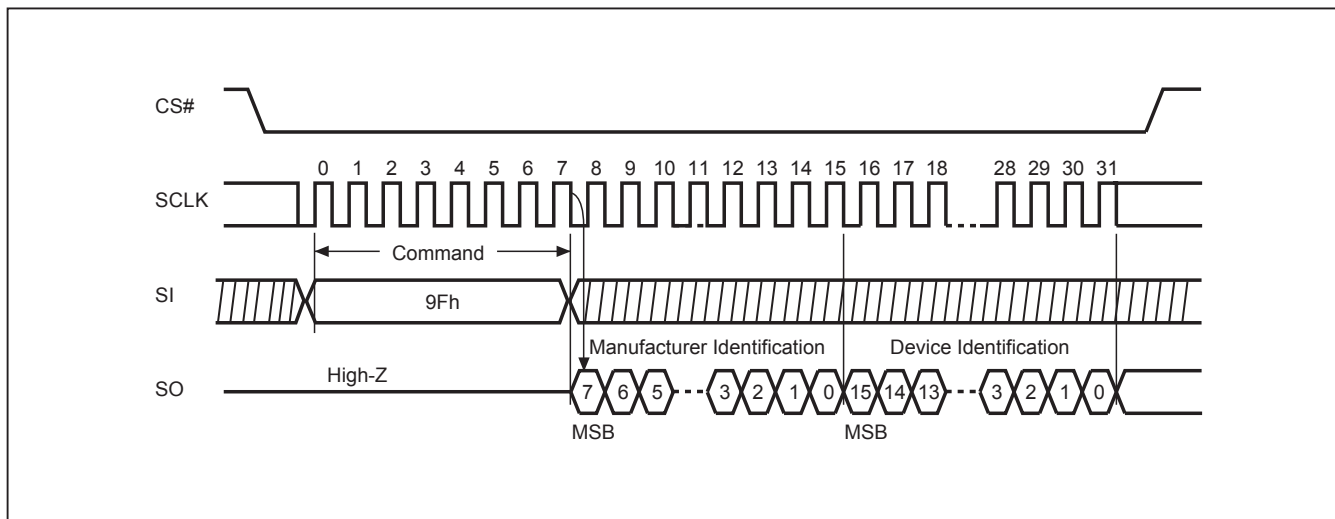
Figure 4. Write Disable (WRDI) Sequence (Command 04)

10-3. Read Identification (RDID)

The RDID instruction is for reading the Manufacturer ID of 1-byte and followed by Device ID of 2-byte. The Macronix Manufacturer ID is C2(hex), the memory type ID is 9E(hex) as the first-byte Device ID, and the individual Device ID of second-byte ID are listed as table of ["Table 7. ID Definitions"](#).

The sequence of issuing RDID instruction is: CS# goes low → sending RDID instruction code → 24-bits ID data out on SO → to end RDID operation can use CS# to high at any time during data out.

While Program/Erase operation is in progress, it will not decode the RDID instruction, so there's no effect on the cycle of program/erase operation which is currently in progress. When CS# goes high, the device is at standby stage.

Figure 5. Read Identification (RDID) Sequence (Command 9F)

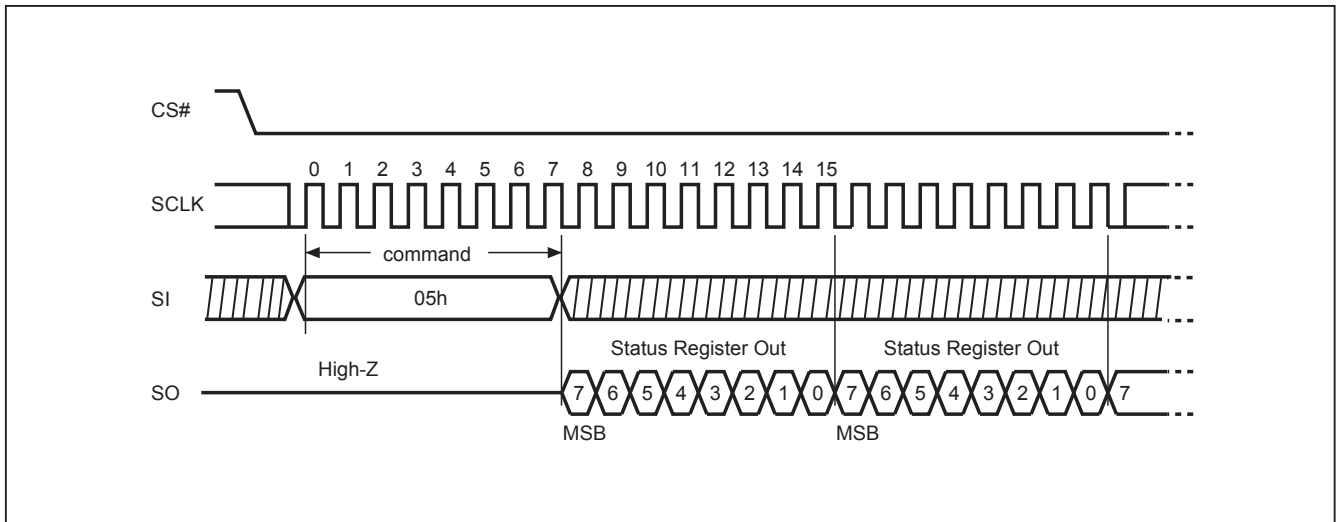
10-4. Read Status Register (RDSR)

The RDSR instruction is for reading Status Register. The Read Status Register can be read at any time (even in program/erase/write status register condition) and continuously. It is recommended to check the Write in Progress (WIP) bit before sending a new instruction when a program, erase, or write status register operation is in progress.

The sequence of issuing RDSR instruction is: CS# goes low→ sending RDSR instruction code→ Status Register data out on SO.

The SIO[3:1] are don't care when during this mode.

Figure 6. Read Status Register (RDSR) Sequence (Command 05)



The definition of the status register bits is as below:

WIP bit. The Write in Progress (WIP) bit, a volatile bit, indicates whether the device is busy in program/erase/write status register progress. When WIP bit sets to 1, which means the device is busy in program/erase/write status register progress. When WIP bit sets to 0, which means the device is not in progress of program/erase/write status register cycle.

WEL bit. The Write Enable Latch (WEL) bit, a volatile bit, indicates whether the device is set to internal write enable latch. When WEL bit sets to "1", which means the internal write enable latch is set, the device can accept program/erase/write status register instruction. When WEL bit sets to 0, which means no internal write enable latch; the device will not accept program/erase/write status register instruction. The program/erase command will be ignored and will reset WEL bit if it is applied to a protected memory area. To ensure both WIP bit & WEL bit are both set to 0 and available for next program/erase/operations, WIP bit needs to be confirm to be 0 before polling WEL bit. After WIP bit confirmed, WEL bit needs to be confirm to be 0.

BP3, BP2, BP1, BP0 bits. The Block Protect (BP3, BP2, BP1, BP0) bits, non-volatile bits, indicate the protected area (as defined in *"Table 2. Protected Area Sizes"*) of the device to against the program/erase instruction without hardware protection mode being set. To write the Block Protect (BP3, BP2, BP1, BP0) bits requires the Write Status Register (WRSR) instruction to be executed. Those bits define the protected area of the memory to against Page Program (PP), Sector Erase (SE), Block Erase (BE) and Chip Erase (CE) instructions (only if all Block Protect bits set to 0, the CE instruction can be executed). The BP3, BP2, BP1, BP0 bits are "0" as default. Which is un-protected.

QE bit. The Quad Enable (QE) bit, non-volatile bit, while it is "0" (factory default), it performs non-Quad and WP# is enable. While QE is "1", it performs Quad I/O mode and WP# is disabled. In the other word, if the system goes into four I/O mode (QE=1), the feature of HPM will be disabled.

SRWD bit. The Status Register Write Disable (SRWD) bit, non-volatile bit, default value is "0". SRWD bit is operated together with Write Protection (WP#/SIO2) pin for providing hardware protection mode. The hardware protection mode requires SRWD sets to 1 and WP#/SIO2 pin signal is low stage. In the hardware protection mode, the Write Status Register (WRSR) instruction is no longer accepted for execution and the SRWD bit and Block Protect bits (BP3, BP2, BP1, BP0) are read only. The SRWD bit defaults to be "0".

Status Register

bit7	bit6	bit5	bit4	bit3	bit2	bit1	bit0
SRWD (status register write protect)	QE (Quad Enable)	BP3 (level of protected block)	BP2 (level of protected block)	BP1 (level of protected block)	BP0 (level of protected block)	WEL (write enable latch)	WIP (write in progress bit)
1=status register write disable	1= Quad Enable 0=not Quad Enable	(note 1)	(note 1)	(note 1)	(note 1)	1=write enable 0=not write enable	1=write operation 0=not in write operation
Non-volatile bit	Non-volatile bit	Non-volatile bit	Non-volatile bit	Non-volatile bit	Non-volatile bit	volatile bit	volatile bit

Note: see the *"Table 2. Protected Area Sizes"* .

Configuration Register

The Configuration Register is able to change the default status of Flash memory. Flash memory will be configured after the CR bit is set.

TB bit

The Top/Bottom (TB) bit is a non-volatile OTP bit. The Top/Bottom (TB) bit is used to configure the Block Protect area by BP bit (BP3, BP2, BP1, BP0), starting from TOP or Bottom of the memory array. The TB bit is defaulted as "0", which means Top area protect. When it is set as "1", the protect area will change to Bottom area of the memory device. To write the TB bit requires the Write Status Register (WRSR) instruction to be executed.

Configuration Register

bit7	bit6	bit5	bit4	bit3	bit2	bit1	bit0
DC (Dummy Cycle)	Reserved	Reserved	Reserved	TB (top/bottom selected)	Reserved	Reserved	Reserved
(Note)	x	x	x	0=Top area protect 1=Bottom area protect (Default=0)	x	x	x
Volatile bit	x	x	x	OTP	x	x	x

Note: See "[Dummy Cycle and Frequency Table](#)", with "Don't Care" on other Reserved Configuration Registers.

Dummy Cycle and Frequency Table

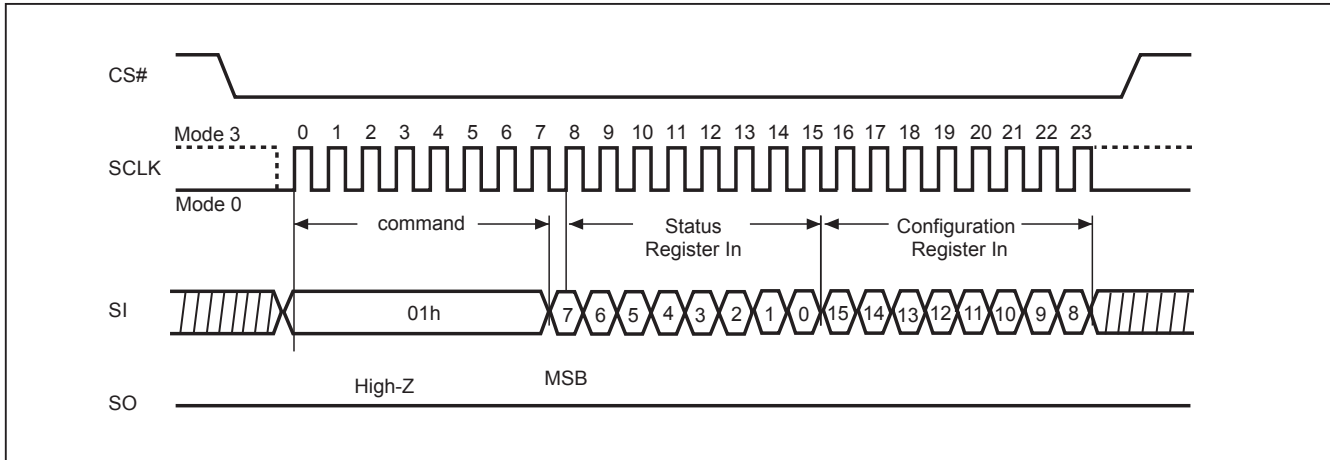
DC	Numbers of Dummy clock cycles	Quad I/O Fast Read
1	8	104
0 (default)	6	86

10-5. Write Status Register (WRSR)

The WRSR instruction is for changing the values of Status Register Bits and Configuration Register Bits. Before sending WRSR instruction, the Write Enable (WREN) instruction must be decoded and executed to set the Write Enable Latch (WEL) bit in advance. The WRSR instruction can change the value of Block Protect (BP3, BP2, BP1, BP0) bits to define the protected area of memory (as shown in "Table 2. Protected Area Sizes"). The WRSR also can set or reset the Quad enable (QE) bit and set or reset the Status Register Write Disable (SRWD) bit in accordance with Write Protection (WP#/SIO2) pin signal, but has no effect on bit1(WEL) and bit0 (WIP) of the status register. The WRSR instruction cannot be executed once the Hardware Protected Mode (HPM) is entered.

The sequence of issuing WRSR instruction is: CS# goes low→ sending WRSR instruction code→ Status Register data on SI→ CS# goes high.

Figure 7. Write Status Register (WRSR) Sequence (Command 01)



The CS# must go high exactly at the byte boundary; otherwise, the instruction will be rejected and not executed. The self-timed Write Status Register cycle time (tW) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be checked out during the Write Status Register cycle is in progress. The WIP sets 1 during the tW timing, and sets 0 when Write Status Register Cycle is completed, and the Write Enable Latch (WEL) bit is reset.

Table 6. Protection Modes

Mode	Status register condition	WP# and SRWD bit status	Memory
Software protection mode (SPM)	Status register can be written in (WEL bit is set to "1") and the SRWD, BP0-BP3 bits can be changed	WP#=1 and SRWD bit=0, or WP#=0 and SRWD bit=0, or WP#=1 and SRWD=1	The protected area cannot be programmed or erased.
Hardware protection mode (HPM)	The SRWD, BP0-BP3 of status register bits cannot be changed	WP#=0, SRWD bit=1	The protected area cannot be programmed or erased.

Note: As defined by the values in the Block Protect (BP3, BP2, BP1, BP0) bits of the Status Register, as shown in "[Table 2. Protected Area Sizes](#)".

As the table above showing, the summary of the Software Protected Mode (SPM) and Hardware Protected Mode (HPM):

Software Protected Mode (SPM):

- When SRWD bit=0, no matter WP#/SIO2 is low or high, the WREN instruction may set the WEL bit and can change the values of SRWD, BP3, BP2, BP1, BP0. The protected area, which is defined by BP3, BP2, BP1, BP0, is at software protected mode (SPM).
- When SRWD bit=1 and WP#/SIO2 is high, the WREN instruction may set the WEL bit can change the values of SRWD, BP3, BP2, BP1, BP0. The protected area, which is defined by BP3, BP2, BP1, BP0, is at software protected mode (SPM)

Hardware Protected Mode (HPM):

- When SRWD bit=1, and then WP#/SIO2 is low (or WP#/SIO2 is low before SRWD bit=1), it enters the hardware protected mode (HPM). The data of the protected area is protected by software protected mode by BP3, BP2, BP1, BP0 and hardware protected mode by the WP#/SIO2 to against data modification.

Note:

To exit the hardware protected mode requires WP#/SIO2 driving high once the hardware protected mode is entered. If the WP#/SIO2 pin is permanently connected to high, the hardware protected mode can never be entered; only can use software protected mode via BP3, BP2, BP1, BP0.

If the system goes into four I/O mode, the feature of HPM will be disabled.